

Technical documentation



Support & training

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# **DRV5032 Ultra-Low-Power Digital-Switch Hall Effect Sensor**

## **1 Features**

- Industry-leading ultra-low power consumption
	- $-$  5-Hz version: 0.54  $\mu$ A with 1.8 V
	- 20-Hz versions: 1.6 µA with 3 V
- 1.65-V to 5.5-V operating  $V_{CC}$  range
- Magnetic threshold options (maximum  $B_{\text{OP}}$ ):
	- 3.9 mT, highest sensitivity
	- 4.8 mT, high sensitivity
	- 9.5 mT, medium sensitivity
	- 63 mT, lowest sensitivity
- Omnipolar and unipolar options
- 20-Hz and 5-Hz sampling rate options
- Open-drain and push-pull output options
- SOT-23, X2SON and TO-92 package options
- -40°C to +85°C operating temperature range

## **2 Applications**

- Battery-critical position sensing
- Electricity meter tamper detection
- Cell Phone, laptop, or tablet case sensing
- E-locks, smoke detectors, appliances
- Medical devices, IoT systems
- Valve or solenoid position detection
- Contactless diagnostics or activation



The DRV5032 device is an ultra-low-power digitalswitch Hall effect sensor, designed for the most compact and battery-sensitive systems. The device is offered in multiple magnetic thresholds, sampling rates, output drivers, and packages to accommodate various applications.

When the applied magnetic flux density exceeds the  $B_{OP}$  threshold, the device outputs a low voltage. The output stays low until the flux density decreases to less than  $B_{RP}$ , and then the output either drives a high voltage or becomes high impedance, depending on the device version. By incorporating an internal oscillator, the device samples the magnetic field and updates the output at a rate of 20 Hz, or 5 Hz for the lowest current consumption. Omnipolar and unipolar magnetic responses are available.

The device operates from a  $V_{CC}$  range of 1.65 V to 5.5 V, and is packaged in a standard SOT-23, TO-92 and small X2SON.



- **Device Information**(1)
- (1) For all available packages, see the orderable addendum at the end of the data sheet.



**Current Consumption of 5-Hz Version**



**Typical Schematic**



# **Table of Contents**





# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.



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## **5 Device Comparison**



### **Table 5-1. Device Comparison**

# **6 Pin Configuration and Functions**















**Figure 6-2. DU Version DBZ Package 3-Pin SOT-23 Top View** 













## **Table 6-1. Pin Functions**

<span id="page-4-0"></span>

## **7 Specifications**

## **7.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted) $(1)$ 



(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### **7.2 ESD Ratings**



(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## **7.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)



### **7.4 Thermal Information**



(1) For more information about traditional and new thermal metrics, see the *[Semiconductor and IC Package Thermal Metrics](https://www.ti.com/lit/pdf/spra953)* application [report.](https://www.ti.com/lit/pdf/spra953)



## <span id="page-5-0"></span>**7.5 Electrical Characteristics**

for  $V_{CC}$  = 1.65 V to 5.5 V, over operating free-air temperature range (unless otherwise noted)



<span id="page-6-0"></span>

## **7.6 Magnetic Characteristics**

for  $V_{CC}$  = 1.65 V to 5.5 V, over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>



(1) For a graphical description of magnetic thresholds, see the *[Magnetic Response](#page-12-0)* section.

(2) X2SON package only.



## <span id="page-7-0"></span>**7.7 Typical Characteristics**





## **7.7 Typical Characteristics (continued)**





## **7.7 Typical Characteristics (continued)**



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## **8 Detailed Description**

## **8.1 Overview**

The DRV5032 device is a magnetic sensor with a digital output that indicates when the magnetic flux density threshold has been crossed. The device integrates a Hall effect element, analog signal conditioning, and a low-frequency oscillator that enables ultra-low average power consumption. By operating from a 1.65-V to 5.5-V supply, the device periodically measures magnetic flux density, updates the output, and enters a low-power sleep state.

### **8.2 Functional Block Diagram**



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## <span id="page-11-0"></span>**8.3 Feature Description**

## **8.3.1 Magnetic Flux Direction**

The DRV5032 device is sensitive to the magnetic field component that is perpendicular to the top of the package (as shown in Figure 8-1).



**Figure 8-1. Direction of Sensitivity**

The magnetic flux that travels from the bottom to the top of the package is considered positive in this data sheet. This condition exists when a south magnetic pole is near the top of the package. The magnetic flux that travels from the top to the bottom of the package results in negative millitesla values.



**Figure 8-2. Flux Direction Polarity**

<span id="page-12-0"></span>

#### **8.3.2 Device Version Comparison**



The following table lists the available device versions.

#### *8.3.2.1 Magnetic Threshold*

Devices that have a lower magnetic threshold detect magnets at a farther distance. Higher thresholds generally require a closer distance or larger magnet.

#### *8.3.2.2 Magnetic Response*

The FA, FB, FC, AJ, and ZE device versions have omnipolar functionality, and these versions all respond to the north and south poles the same way as shown in Figure 8-3.



**Figure 8-3. Omnipolar Functionality**

The DU and FD device versions have unipolar functionality. Pin OUT1 only responds to flux in the top-down direction (north), and pin OUT2 only responds to flux in the bottom-up direction (south).





### *8.3.2.3 Output Type*

The DU, FA, FB, and FD device versions have push-pull CMOS outputs that can drive a  $V_{CC}$  or ground level. The FC, AJ, and ZE device versions have open-drain outputs that can become high impedance or drive ground. For these versions, an external pullup resistor must be used.



**Figure 8-5. Push-Pull Output (Simplified)**



**Figure 8-6. Open-Drain Output (Simplified)**

#### *8.3.2.4 Sampling Rate*

When the DRV5032 device powers up, it measures the first magnetic sample and sets the output within the  $t_{ON}$ time. The output is latched, and the device enters an ultra-low-power sleep state. After each  $t<sub>S</sub>$  time, the device measures a new sample and updates the output, if necessary. If the magnetic field does not change between periods, the output does not change.

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**Figure 8-7. Timing Diagram**



#### <span id="page-15-0"></span>**8.3.3 Hall Element Location**

The sensing element inside the device is in the center of both packages when viewed from the top. Figure 8-8 shows the tolerances and side-view dimensions.



**Figure 8-8. Hall Element Location**

### **8.4 Device Functional Modes**

The DRV5032 device has one mode of operation that applies when the *[Recommended Operating Conditions](#page-4-0)* are met.

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## **9 Application and Implementation**

#### **Note**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### **9.1 Application Information**

The DRV5032 device is typically used to detect the proximity of a magnet. The magnet is often attached to a movable component in the system.

#### **9.1.1 Output Type Tradeoffs**

The push-pull output allows for the lowest system power consumption because there is no current leakage path when the output drives high or low. The open-drain output involves a leakage path through the external pullup resistor when the output drives low.

The open-drain outputs of multiple devices can be tied together to form a logical AND. In this setup, if any sensor drives low, the voltage on the shared node becomes low. This can allow a single GPIO to measure an array of sensors.

### **9.2 Typical Applications**

#### **9.2.1 General-Purpose Magnet Sensing**



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**Figure 9-1. Typical Application Diagram**

#### *9.2.1.1 Design Requirements*

For this design example, use the parameters listed in Table 9-1.



#### *9.2.1.2 Detailed Design Procedure*

When designing a digital-switch magnetic sensing system, the user should consider these three variables: the magnet, sensing distance, and threshold of the sensor.

#### **[DRV5032](https://www.ti.com/product/DRV5032)** [SLVSDC7F](https://www.ti.com/lit/pdf/SLVSDC7) – APRIL 2017 – REVISED FEBRUARY 2022 **[www.ti.com](https://www.ti.com)**



The DRV5032 device has a detection threshold specified by parameter  $B_{OP}$ . To reliably activate the sensor, the magnet must apply greater than the maximum specified  $B_{OP}$ . In such a system, the sensor typically detects the magnet before it has moved to the closest position. When the magnet moves away from the sensor, it must apply less than the minimum specified  $B_{RP}$  to reliably release the sensor.

Magnets are made from various ferromagnetic materials that have trade-offs in cost, drift with temperature, absolute max temperature ratings, remanence or residual induction (B<sub>r</sub>), and coercivity (H<sub>c</sub>). The B<sub>r</sub> and the dimensions of a magnet determine the magnetic flux density (B) it produces in 3-dimensional space. For simple magnet shapes, such as rectangular blocks and cylinders, there are simple equations that solve B at a given distance centered with the magnet.



### **Figure 9-2. Rectangular Block and Cylinder Magnets**

Use Equation 1 for the rectangular block shown in Figure 9-2:

$$
\vec{B} = \frac{B_r}{\pi} \left( \arctan\left(\frac{WL}{2D\sqrt{4D^2 + W^2 + L^2}}\right) - \arctan\left(\frac{WL}{2(D+T)\sqrt{4(D+T)^2 + W^2 + L^2}}\right) \right) \tag{1}
$$

Use Equation 2 for the cylinder shown in Figure 9-2:

$$
\vec{B} = \frac{B_r}{2} \left( \frac{D + T}{\sqrt{(0.5C)^2 + (D + T)^2}} - \frac{D}{\sqrt{(0.5C)^2 + D^2}} \right)
$$
(2)

where

- W is width.
- L is length.
- T is thickness (the direction of magnetization).
- D is distance.
- C is diameter.

An online tool that uses these formulas is located at [http://www.ti.com/product/drv5033.](http://www.ti.com/product/drv5033)

All magnetic materials generally have a lower  $\mathsf{B}_\mathsf{r}$  at higher temperatures. Systems should have margin to account for this, as well as for mechanical tolerances.



#### *9.2.1.3 Application Curve*



**Figure 9-3. Magnetic Profile of a 1-cm Cube NdFeB Magnet**

#### **9.2.2 Three-Position Switch**

This application uses the DRV5032FD for a three-position switch.



**Figure 9-4. Three-Position Slider Switch With Embedded Magnet**

#### *9.2.2.1 Design Requirements*

For this design example, use the parameters listed in Table 9-2.



#### **Table 9-2. Design Parameters**

#### *9.2.2.2 Detailed Design Procedure*

A standard 2-pole magnet produces strong perpendicular flux components near the outer edges of the poles, and no perpendicular flux near the center at the north-south pole boundary. When the DRV5032FD is below the center of the magnet, it receives close to 0 mT, and both outputs drive high. If the switch with the embedded magnet moves left or right, the sensor receives a north or south field, and OUT1 or OUT2 drive low. This provides 3 digital states of detection.

The length of the magnet should ideally be two times the distance of travel toward each side. Then, when the switch is pushed to either side, the outer edge of the magnet is positioned directly above the sensor where it applies the strongest perpendicular flux component.



To determine the magnitude of magnetic flux density for a given magnet and distance, TI recommends to either use simulation software, test with a linear Hall effect sensor, or test with a gaussmeter.

#### *9.2.2.3 Application Curve*

Figure 9-5 shows the typical magnetic flux lines around a 2-pole magnet.



**Figure 9-5. Typical Magnetic Flux Lines**

<span id="page-20-0"></span>

## **9.3 Do's and Don'ts**

The Hall element is sensitive to magnetic fields that are perpendicular to the top of the package, therefore a correct magnet approach must be used for the sensor to detect the field. Figure 9-6 shows correct and incorrect approaches.



**Figure 9-6. Correct and Incorrect Magnet Approaches**



## <span id="page-21-0"></span>**10 Power Supply Recommendations**

The DRV5032 device is powered from 1.65-V to 5.5-V DC power supplies. A decoupling capacitor close to the device must be used to provide local energy with minimal inductance. TI recommends using a ceramic capacitor with a value of at least 0.1 µF.

## **11 Layout**

## **11.1 Layout Guidelines**

Magnetic fields pass through most nonferromagnetic materials with no significant disturbance. It is common practice to embed Hall effect sensors within plastic or aluminum enclosures and sensing magnets on the outside. Magnetic fields also easily pass through most printed-circuit boards, which makes placing the magnet on the opposite side possible.

### **11.2 Layout Examples**



**Figure 11-1. Layout Examples**

<span id="page-22-0"></span>

## **12 Device and Documentation Support**

### **12.1 Documentation Support**

#### **12.1.1 Related Documentation**

For related documentation see the following:

- Texas Instruments, *[DRV5032-SOLAR-EVM](https://www.ti.com/lit/pdf/SLVUB45)* user's guide
- Texas Instruments, *[Power Gating Systems with Magnetic Sensors](https://www.ti.com/lit/pdf/SBOA196)* TI TechNote
- Texas Instruments, *[Low-Power Door and Window Sensor With Sub-1GHz and 10-Year Coin Cell Battery Life](https://www.ti.com/lit/pdf/TIDUC69)*
- Texas Instruments, *[Magnetic Tamper Detection Using Low-Power Hall Effect Sensors](https://www.ti.com/lit/pdf/TIDUB69)*
- Texas Instruments, *[Fault Monitoring for Overhead Fault Indicators Using Ultra-Low-Power](https://www.ti.com/lit/pdf/TIDUBY5)*

#### **12.2 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on [ti.com.](https://www.ti.com) Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **12.3 Support Resources**

TI E2E™ [support forums](https://e2e.ti.com) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### **12.4 Trademarks**

TI E2E™ is a trademark of Texas Instruments.

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#### **12.5 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### **12.6 Glossary**

[TI Glossary](https://www.ti.com/lit/pdf/SLYZ022) This glossary lists and explains terms, acronyms, and definitions.

### **13 Mechanical, Packaging, and Orderable Information**

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## **PACKAGING INFORMATION**





**(1)** The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures. "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the  $\leq 1000$ ppm threshold requirement.

**(3)** MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

**(4)** There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

**(5)** Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

**(6)** Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

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### **TAPE AND REEL INFORMATION**

**ISTRUMENTS** 





#### **QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**







# **PACKAGE MATERIALS INFORMATION**

www.ti.com 20-Feb-2024







# **PACKAGE OUTLINE**

# **DBZ0003A SOT-23 - 1.12 mm max height**

SMALL OUTLINE TRANSISTOR



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. Reference JEDEC registration TO-236, except minimum foot length.
- 4. Support pin may differ or may not be present.



# **EXAMPLE BOARD LAYOUT**

# **DBZ0003A SOT-23 - 1.12 mm max height**

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# **EXAMPLE STENCIL DESIGN**

# **DBZ0003A SOT-23 - 1.12 mm max height**

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

7. Board assembly site may have different recommendations for stencil design.





# **PACKAGE OUTLINE**

TRANSISTOR OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



# **EXAMPLE BOARD LAYOUT**

# **LPG0003A TO-92 - 5.05 mm max height**

TRANSISTOR OUTLINE





# **TAPE SPECIFICATIONS**

# **LPG0003A TO-92 - 5.05 mm max height**

TRANSISTOR OUTLINE





# **GENERIC PACKAGE VIEW**

# **DMR 4 X2SON - 0.4 mm max height**

**1.1 x 1.4, 0.5 mm pitch PLASTIC SMALL OUTLINE - NO LEAD** 

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







# **PACKAGE OUTLINE**

# **DMR0004A X2SON - 0.4 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
- 4. Quantity and shape of side wall metal may vary.



# **EXAMPLE BOARD LAYOUT**

# **DMR0004A X2SON - 0.4 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

6. Vias are optional depending on application, refer to device data sheet. If all or some are implemented, recommended via locations are shown. It is recommended that vias under paste be filled, plugged or tented.



# **EXAMPLE STENCIL DESIGN**

# **DMR0004A X2SON - 0.4 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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